Abstracts

CW Gunn Diodes in Composite Structure (Correspondence)

S. Mitsui. "CW Gunn Diodes in Composite Structure (Correspondence)." 1969 Transactions on Microwave Theory and Techniques 17.12 (Dec. 1969 [T-MTT]): 1158-1160.

Parallel combinations of Gunn diodes for X-band are fabricated with three types of n-type GaAs crystals. The diodes are mesa structured and mounted upside down on a copper stud of a package in parallel combination. An output power of 450 mW in CW operation at an efficiency of 2.9 percent is obtained in a double-mounted diode at 9 GHz.

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